CLAIMS

1. A solar cell comprising a gallium-doped silicon substrate having a p-n junction formed therein,

wherein the silicon substrate is provided with a silicon thermal oxide film at least on a first main surface of main surfaces of the silicon substrate, the first main surface being a main surface having a p-type region,

the silicon substrate is further doped with boron, and

the silicon substrate has a boron concentration of 5×10^{14} atoms/cm^3 or more and 1×10^{16} atoms/cm^3 or less.

2. The solar cell according to claim 1, wherein, in the silicon substrate, at least the first main surface is a p-type entirely.

3. A method for manufacturing a solar cell, comprising the steps of:

preparing a silicon substrate doped with gallium and boron;

forming a p-n junction in the silicon substrate; and

forming a silicon thermal oxide film at least on a first main surface of main surfaces of the silicon substrate, the first main surface being a main surface having a p-type region,

wherein the silicon substrate to be prepared has a boron concentration of 5×10^{14} atoms/cm^3 or more and 1×10^{16} atoms/cm^3 or less.